Abstracts

Pseudomorphic Inverted HEMT Suitable to Low Supplied Voltage Application (1992 Vol. II [MWSYM])

M. Kasashima, Y. Arai, H.I. Fujishiro, H. Nakamura and S. Nishi. "Pseudomorphic Inverted HEMT Suitable to Low Supplied Voltage Application (1992 Vol. II [MWSYM])." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 651-654.

The superiority of pseudomorphic inverted HEMT as a promising low-voltage-operating device was revealed. To study the high frequency properties of FET, two types of frequency variable measurement systems which represent active load and common-source circuits were employed. It was confirmed that the feature of low knee voltage in static I-V is preserved above 100kHz, which predicts the microwave characteristics of the device. Estimated output power was 50% higher than that of conventional pseudomorphic HEMT at V/sub dd/=1V.

❑ Return to main document.